



2.4 GHz High-Power, High-Gain Power Amplifier

SST12LP08A

Data Sheet

Product Description

The SST12LP08A is a versatile power amplifier based on the highly-reliable InGaP/GaAs HBT technology.

The SST12LP08A can be easily configured for high-power applications with good power-added efficiency while operating over the 2.4- 2.5 GHz frequency band. It typically provides 29 dB gain with 34% power-added efficiency (PAE) @ POUT = 24 dBm for 802.11g and 31% PAE @ POUT = 23.5 dBm for 802.11b

The SST12LP08A has excellent linearity, typically ~3% added EVM at 20 dBm output power which is essential for 54 Mbps 802.11g operation while meeting 802.11g spectrum mask at 24 dBm.

The SST12LP08A also features easy board-level usage along with high-speed power-up/down control through a single combined reference voltage pin. Ultra-low reference current (total I_{REF} ~2 mA) makes the SST12LP08A controllable by an on/off switching signal directly from the baseband chip. These features, coupled with low operating current, make the SST12LP08A ideal for the final stage power amplification in battery-powered 802.11b/g/n WLAN transmitter applications.

The SST12LP08A has an excellent on-chip, single-ended power detector, which features wide-range (>15 dB) with dB-wise linearization. The excellent on-chip power detector provides a reliable solution to board-level power control.

The SST12LP08A is offered in 8-contact XSON package. See Figure 2 for pin assignments and Table 1 for pin descriptions.



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Functional Blocks

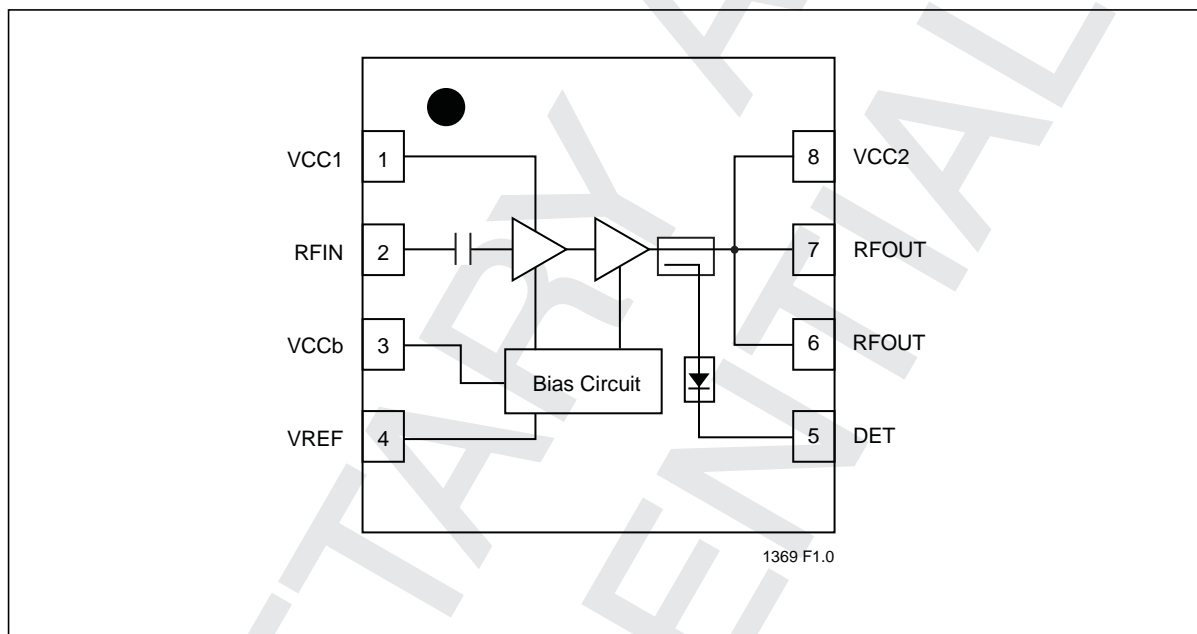


Figure 1: Functional Block Diagram



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Pin Assignments

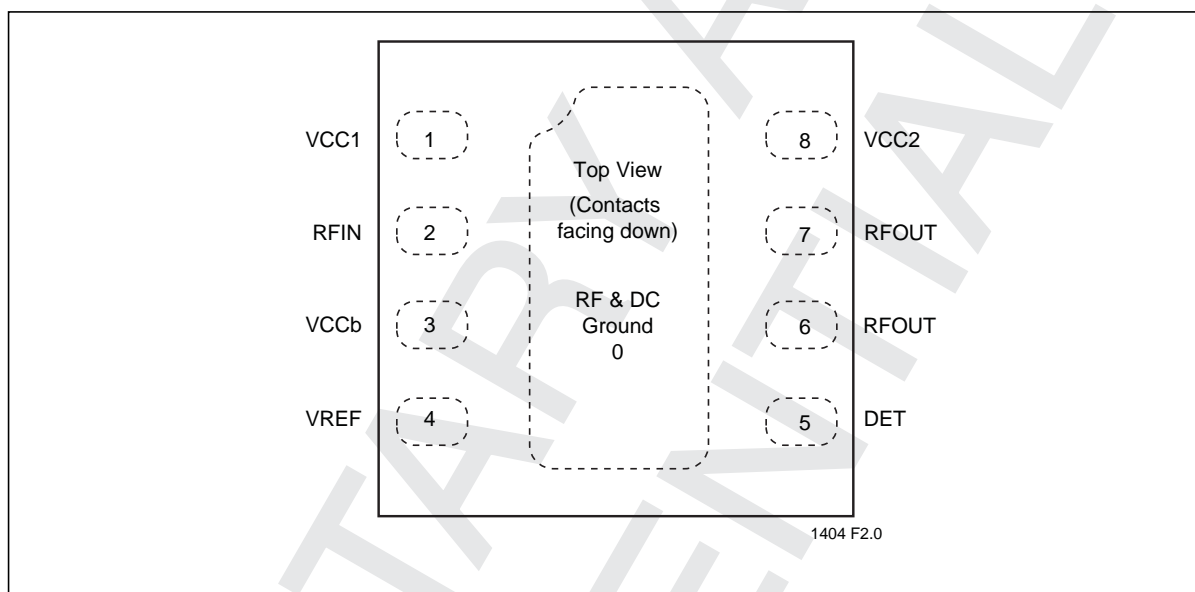


Figure 2: Pin Assignments for 8-contact XSON

Pin Descriptions

Table 1: Pin Description

Symbol	Pin No.	Pin Name	Type ¹	Function
GND	0	Ground		Low inductance GND pad
V _{CC1}	1	Power Supply	PWR	Power supply, 1 st stage
R _F IN	2		I	RF input, DC decoupled
V _{CCb}	3	Power Supply	PWR	Supply voltage for bias circuit
VREF	4		PWR	1 st and 2 nd stage idle current control
Det	5		O	On-chip power detector
RFOUT	6		O	RF output
RFOUT	7		O	RF output
V _{CC2}	8	Power Supply	PWR	Power supply, 2 nd stage

1. I=Input, O=Output

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Electrical Specifications

The AC and DC specifications for the power amplifier interface signals. Refer to Table 3 for the DC voltage and current specifications. Refer to Figures 3 through 10 for the RF performance.

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Input power to pin 2 (P_{IN})	+5 dBm
Average output power (P_{OUT}) ¹	+26 dBm
Supply Voltage at pins 1, 3, and 8 (V_{CC})	-0.3V to +4.6V
Reference voltage to pin 4 (V_{REF})	-0.3V to +3.3V
DC supply current (I_{CC}) ²	400 mA
Operating Temperature (T_A)	-40°C to +85°C
Storage Temperature (T_{STG})	-40°C to +120°C
Maximum Junction Temperature (T_J)	+150°C
Surface Mount Solder Reflow Temperature	260°C for 10 seconds

1. Never measure with CW source. Pulsed single-tone source with <50% duty cycle is recommended. Exceeding the maximum rating of average output power could cause permanent damage to the device.

2. Measured with 100% duty cycle 54 Mbps 802.11g OFDM Signal

Table 2: Operating Range

Range	Ambient Temp	V_{CC}
Industrial	-40°C to +85°C	3.3V

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Table 3: DC Electrical Characteristics at 25°C

Symbol	Parameter	Min.	Typ	Max.	Unit	Test Conditions
V_{CC}	Supply Voltage at pins 1,3,and 8	3.0	3.3	4.2	V	
I_{CC}	Supply Current					
	for 802.11g, 24 dBm		220		mA	
	for 802.11b, 23.5 dBm		215		mA	
I_{CQ}	Idle current for 802.11g to meet EVM ~3% @ 20 dBm		78		mA	
V_{REG}	Reference Voltage with 130Ω resistor	2.75	2.85	2.95	V	

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Table 4: AC Electrical Characteristics for Configuration at 25°C

Symbol	Parameter	Min.	Typ	Max.	Unit
F _{L-U}	Frequency range	2412		2484	MHz
G	Small signal gain	28	29		dB
G _{VAR1}	Gain variation over band (2412–2484 MHz)			±0.5	dB
G _{VAR2}	Gain ripple over channel (20 MHz)		0.2		dB
ACPR	Meet 11b spectrum mask	23			dBm
	Meet 11g OFDM 54 Mbps spectrum mask	23.5			dBm
Added EVM	@ 20 dBm output with 11g OFDM 54 Mbps signal		2.5	3	%
2f, 3f, 4f, 5f	Harmonics at 22 dBm, without external filters			-40	dBc

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Typical Performance Characteristics

Test Conditions: $V_{CC} = 3.3V$, $T_A = 25^\circ C$, unless otherwise specified

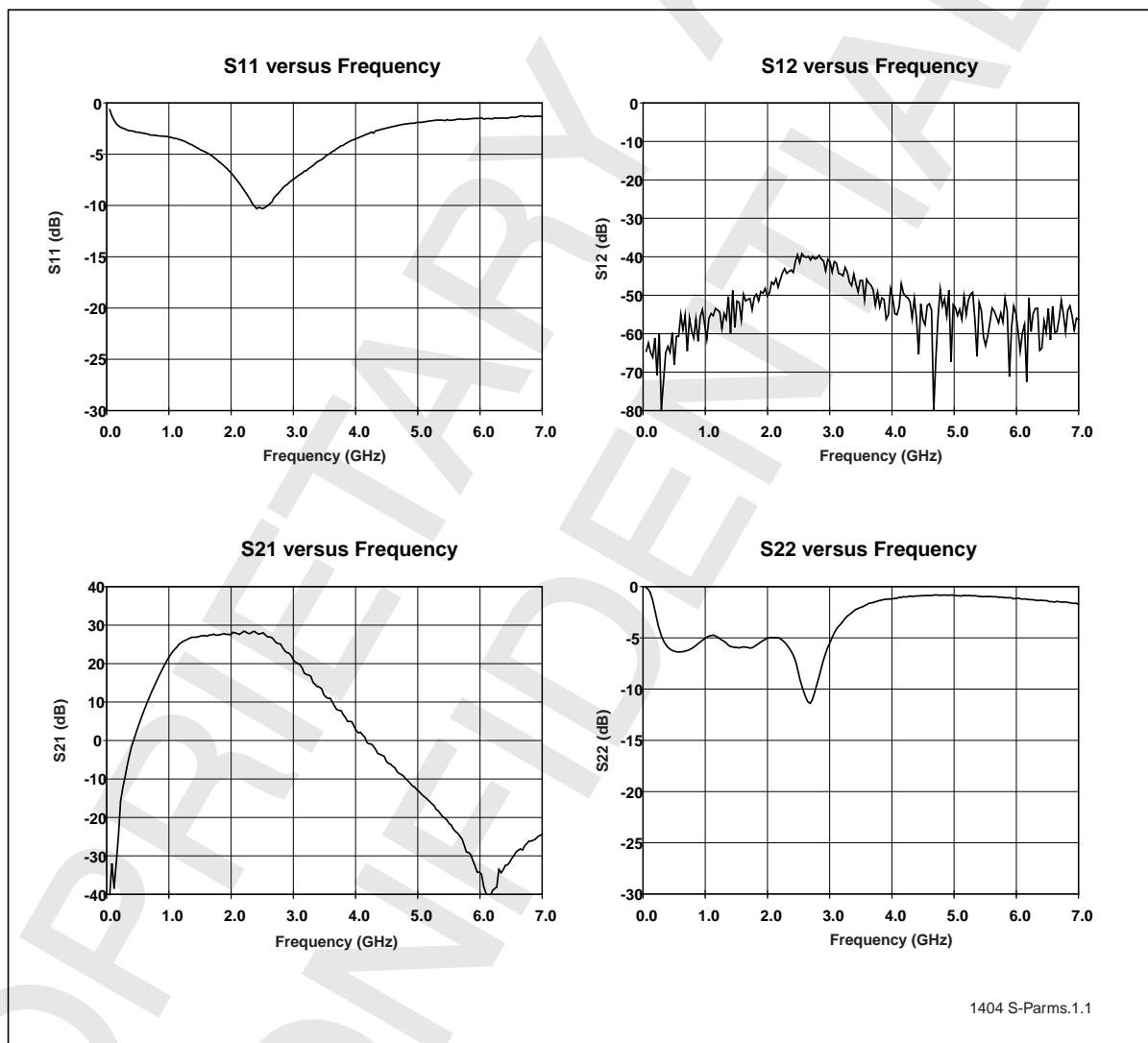


Figure 3: S-Parameters



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Typical Performance Characteristics

Test Conditions: $V_{CC} = 3.3V$, $T_A = 25^\circ C$, 54 Mbps 802.11g OFDM signal

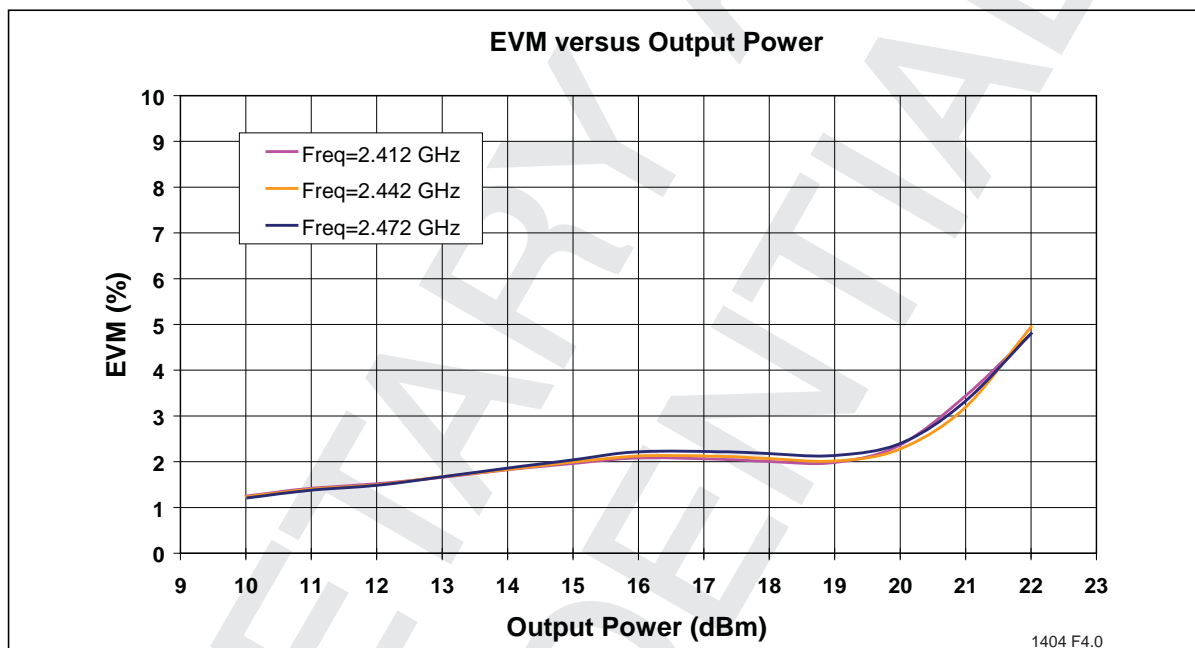


Figure 4: EVM versus Output Power measured with Data plus Sequence equalizer training

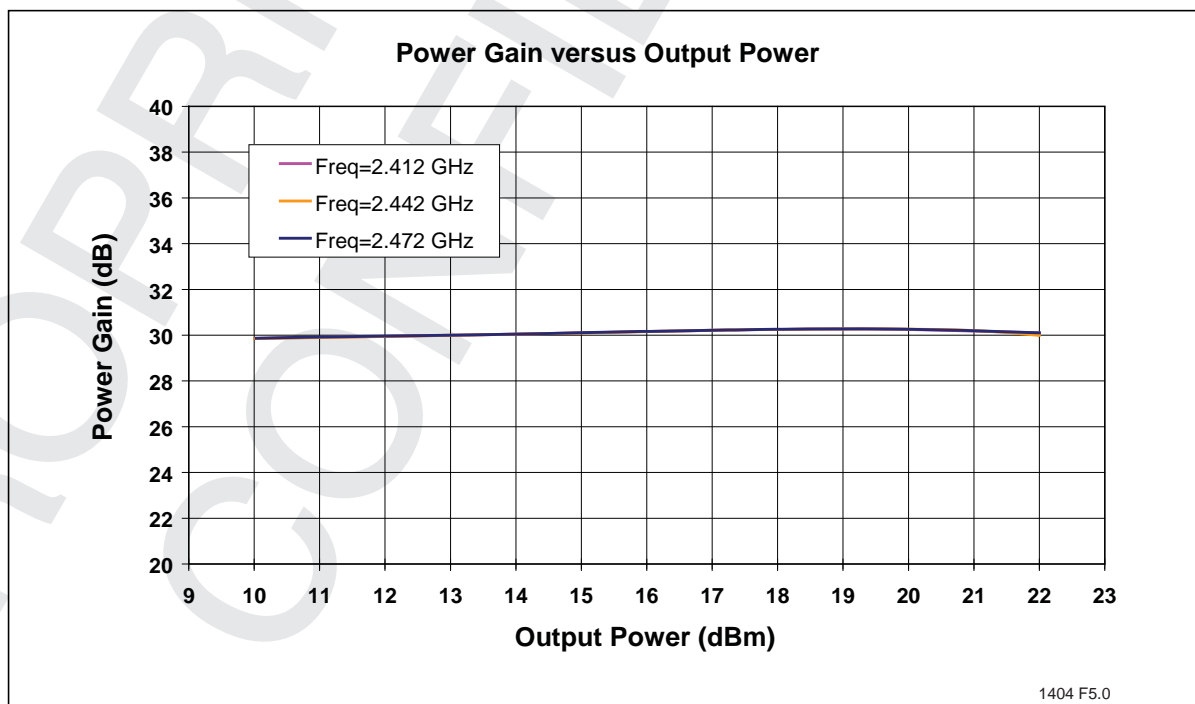


Figure 5: Power Gain versus Output Power



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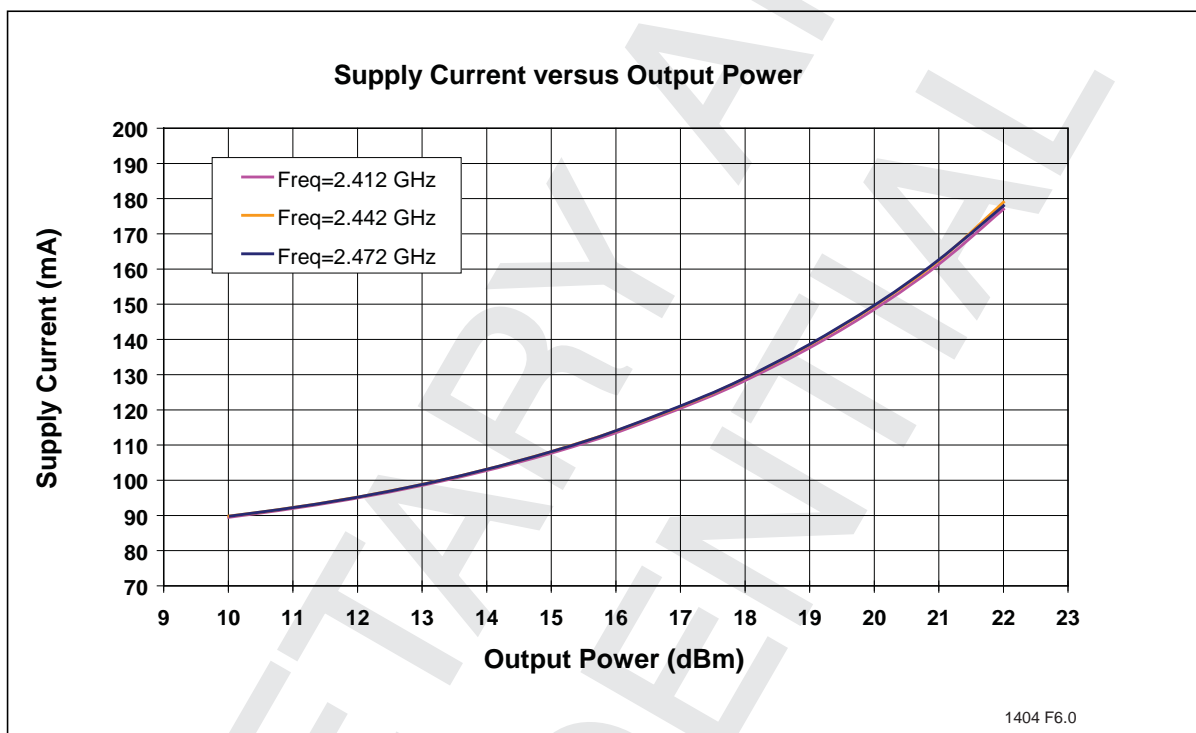


Figure 6: Total Current Consumption for 802.11g operation versus Output Power

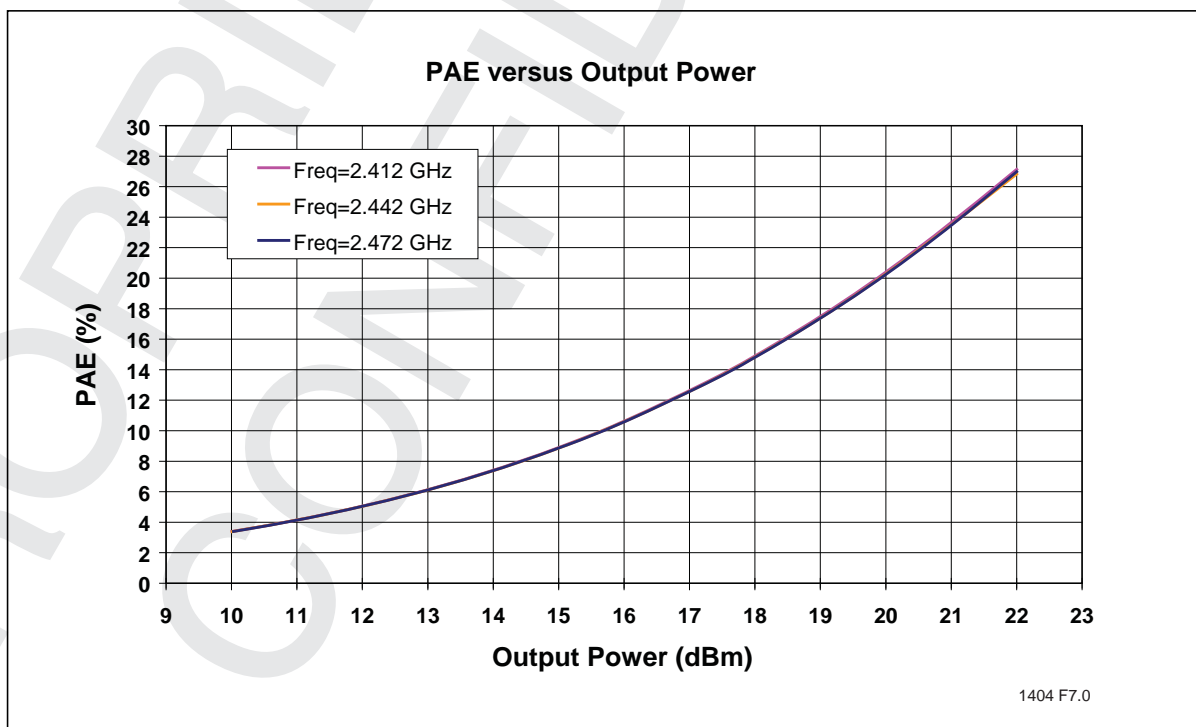


Figure 7: PAE versus Output Power



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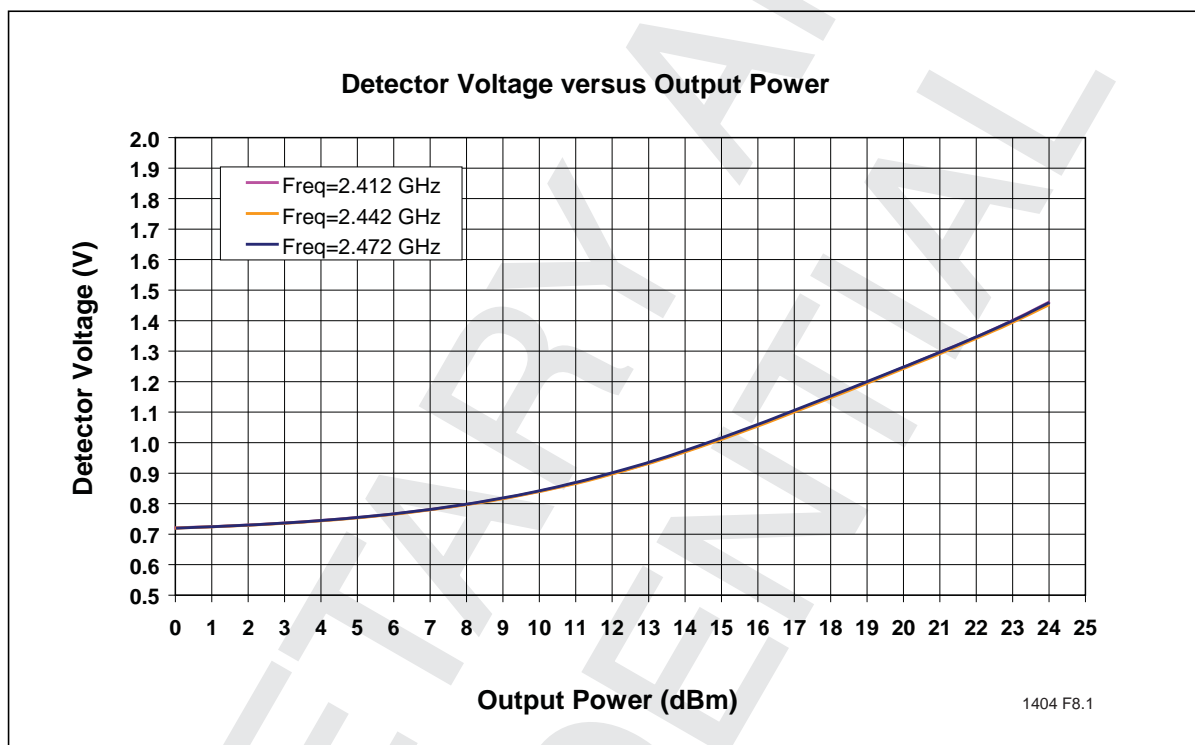


Figure 8: Detector Characteristics versus Output Power

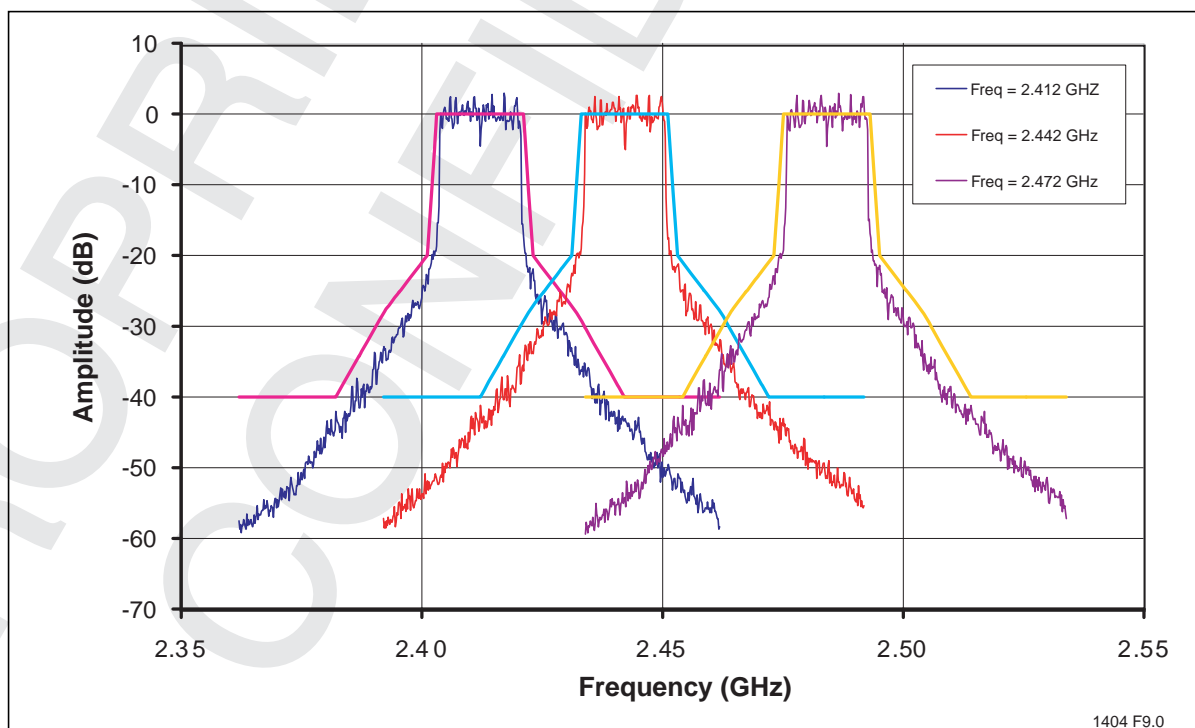


Figure 9: 802.11g Spectrum Mask at 24 dBm, Total Current 220 mA



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Typical Performance Characteristics

Test Conditions: $V_{CC} = 3.3V$, $T_A = 25^\circ C$, 1 Mbps 802.11b CCK Signal

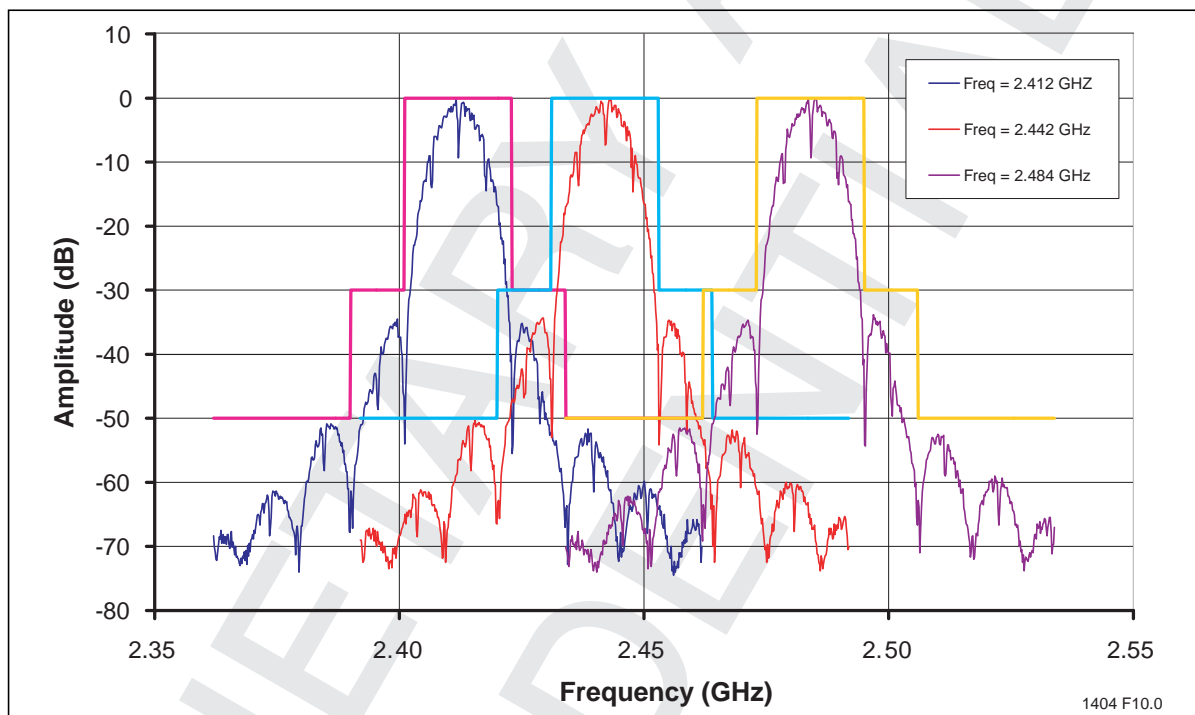


Figure 10: 802.11b Spectrum Mask at 23.5 dBm, Total Current 215 mA



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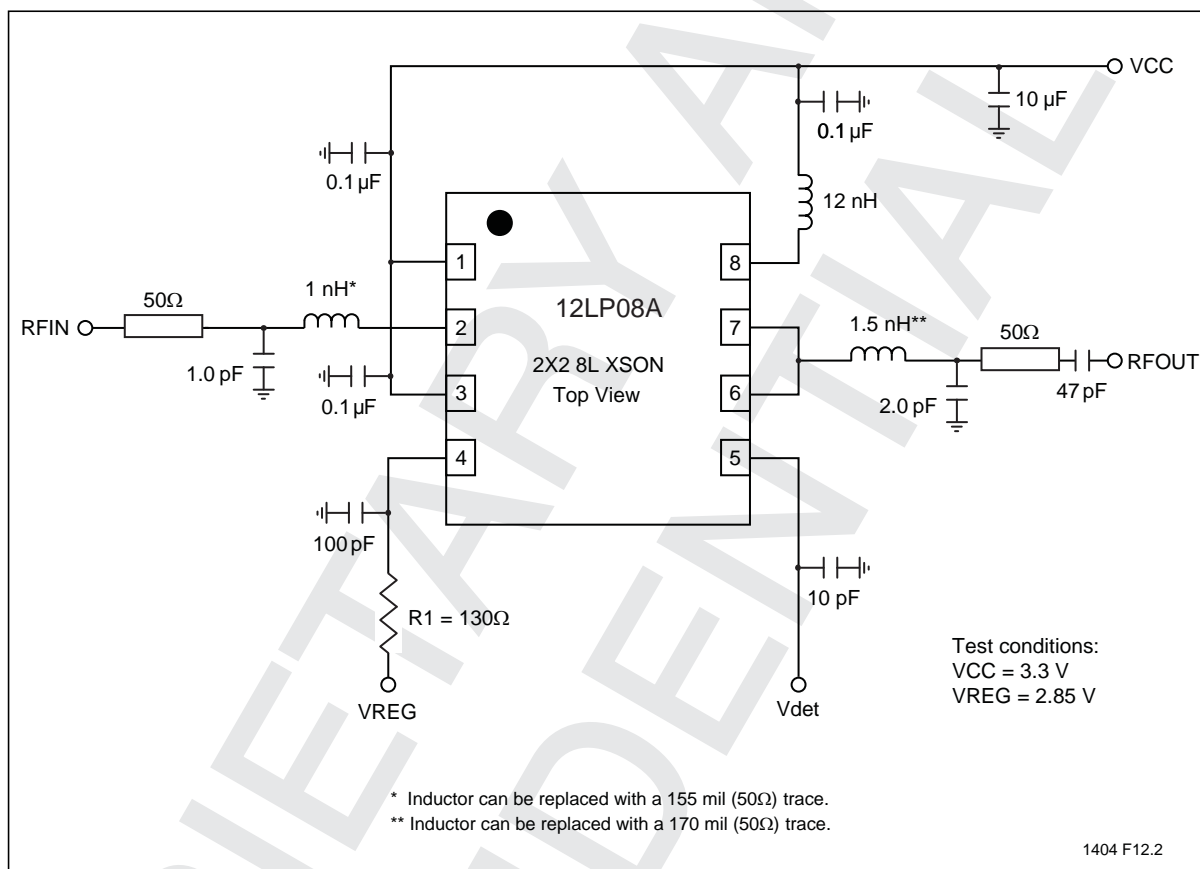


Figure 11: Typical Schematic for High-Power/High-Efficiency 802.11b/g Applications

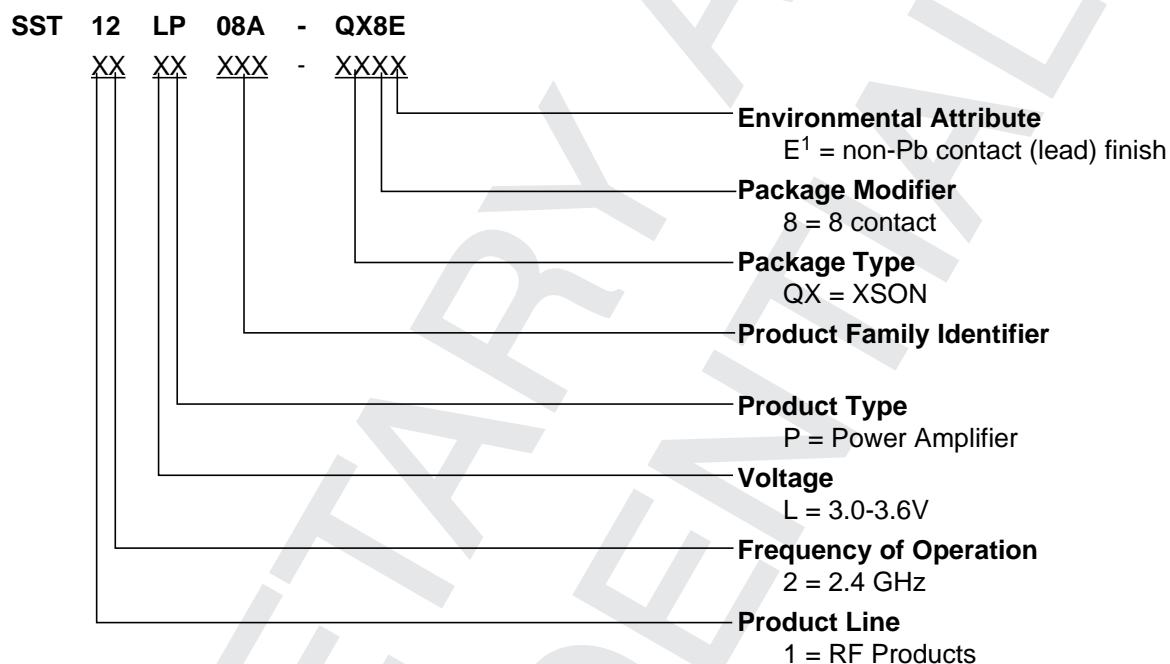


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Product Ordering Information



1. Environmental suffix "E" denotes non-Pb solder. SST non-Pb solder devices are "RoHS Compliant".

Valid combinations for SST12LP08A

SST12LP08A-QX8E

SST12LP08A Evaluation Kits

SST12LP08A-QX8E-K

Note: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.



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Packaging Diagrams

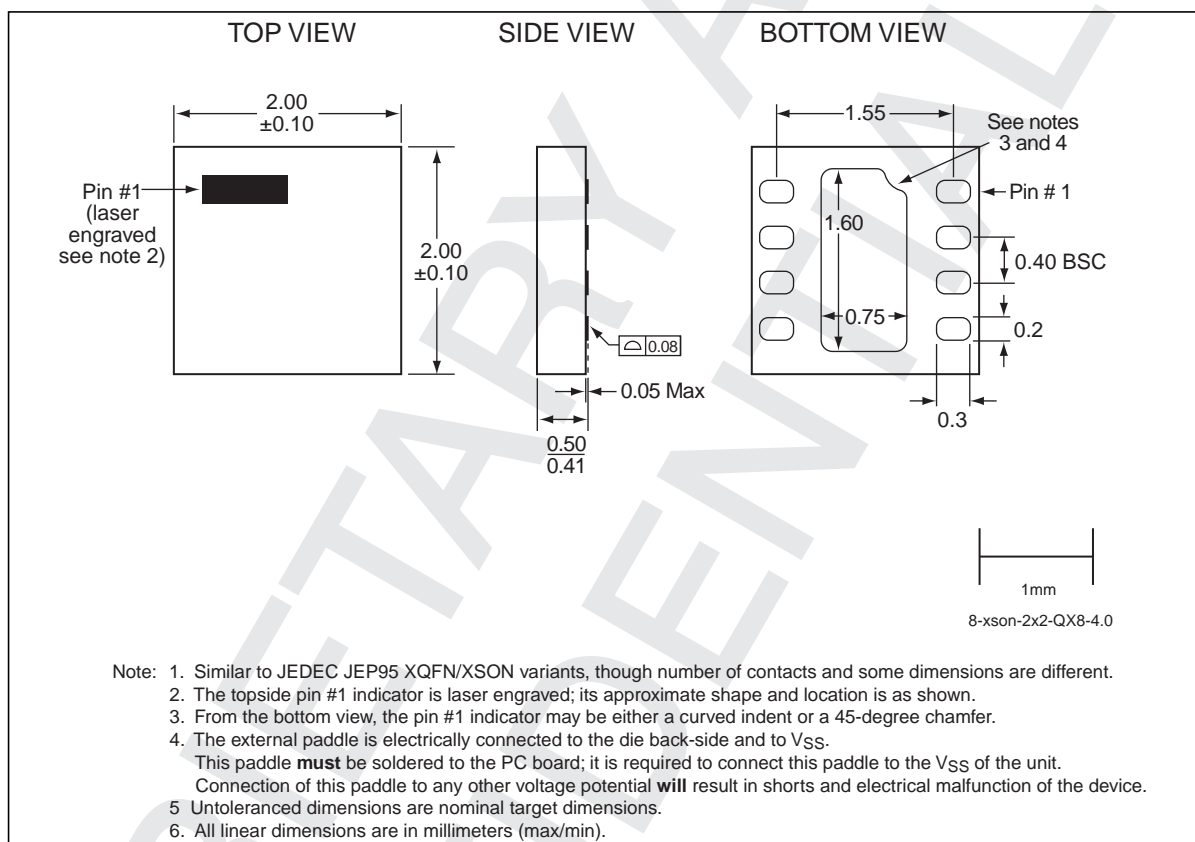


Figure 12: 8-Contact Extremely-thin Small Outline No-lead (XSON)
SST Package Code: QX8



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Table 5: Revision History

Revision	Description	Date
00	• Initial release of data sheet	Mar 2009
01	• Changed product number from SST12LP08 to SST12LP08A.	Apr 2009
02	• Updated Product Description and Table 3 • Revised temperature information in Table 2	Sep 2009
03	• Changed document status to "Data Sheet."	Feb 2010
A	• Applied new document format • Released document under letter revision system • Updated Spec number from S71404 to DS75055 • Updated "Features" on page 1 and Table 2 on page 5 to reflect an Industrial temperature range. • Updated max V_{CC} from 3.6V to 4.2V in Table 3 on page 5 • Updated supply voltage from 4.0V to 4.6V in "Absolute Maximum Stress Ratings" on page 5 • Updated Figure 12 to reflect new Pin 1 indicator • Revised caption for Figure 4 on page 8	Jul 2012

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